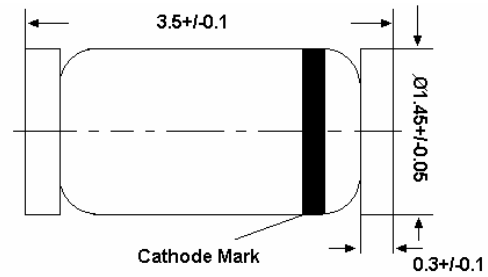


LL916, LL916A, LL916B

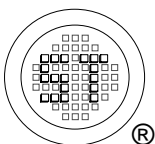
HIGH CONDUCTANCE FAST DIODES



Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Working Inverse Voltage	W_{IV}	75	V
Average Rectified Current	I_O	200	mA
DC Forward Current	I_F	300	mA
Recurrent Peak Forward Current	i_f	400	mA
Peak Forward Surge Current			
Pulse width = 1 second	$i_{f(\text{surge})}$	1	A
Pulse width = 1 microsecond	$i_{f(\text{surge})}$	4	A
Total Device Dissipation		500	mW
Derate above 25°C	P_D	3.33	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	300	$^\circ\text{C}/\text{W}$
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_s	-65 to +200	$^\circ\text{C}$



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ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

Dated : 13/04/2002

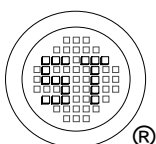
LL916, LL916A, LL916B

Characteristics at $T_A = 25^\circ\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
Breakdown Voltage at $I_R = 100\mu\text{A}$ at $I_R = 5\mu\text{A}$	B_V	100	-	-	V
	B_V	75	-	-	V
Reverse Current at $V_R = 20\text{V}$ at $V_R = 20\text{V}, T_A = 150^\circ\text{C}$ at $V_R = 75\text{V}$	I_R	-	-	25	nA
	I_R	-	-	50	μA
	I_R	-	-	5	μA
Forward Voltage at $I_F = 5\text{mA}$ at $I_F = 10\text{mA}$ at $I_F = 20\text{mA}$ at $I_F = 30\text{mA}$	LL916B V_F	630	-	730	mV
	LL916 V_F	-	-	1	V
	LL916A V_F	-	-	1	V
	LL916B V_F	-	-	1	V
Diode Capacitance at $f = 1\text{MHz}$	C_O	-	-	2	pF
Reverse Recovery Time at $I_F = 10\text{mA}, V_R = 6\text{V}(60\text{mA}),$ $I_{RR} = 1.0\text{mA}, R_L = 100\Omega$	t_{rr}	-	-	4	ns

Notes:(1) These ratings are based on a maximum junction temperature of 200 degrees C.

(2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.



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Certificate No. 71116

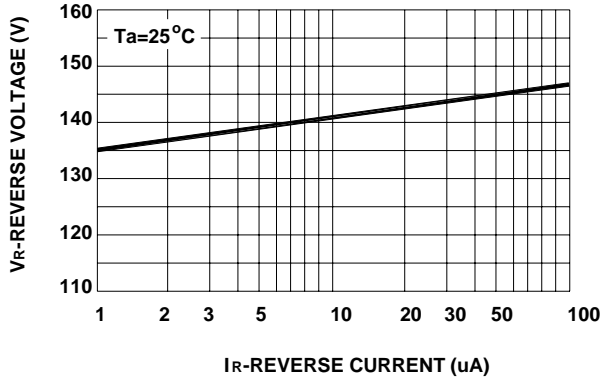


ISO 9001:2000
Certificate No. 0506098

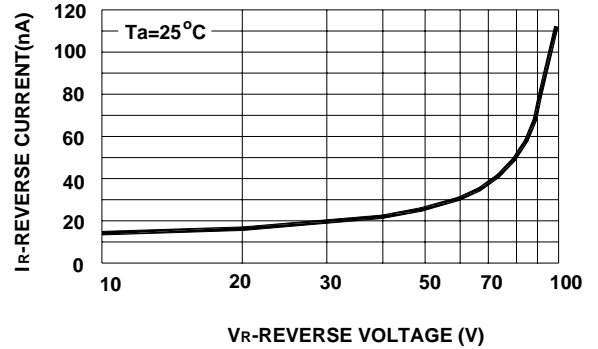
Dated : 13/04/2002

Typical Characteristics

REVERSE VOLTAGE vs REVERSE CURRENT
BV-1.0 to 100 μ A

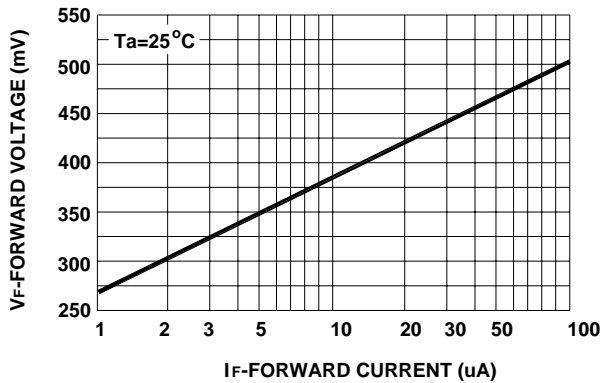


REVERSE CURRENT vs REVERSE VOLTAGE
IR-10 to 100 V

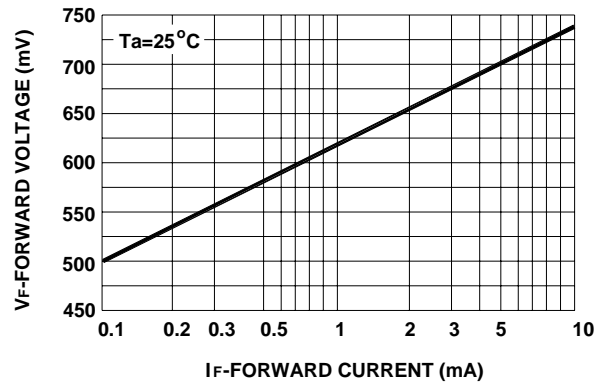


GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

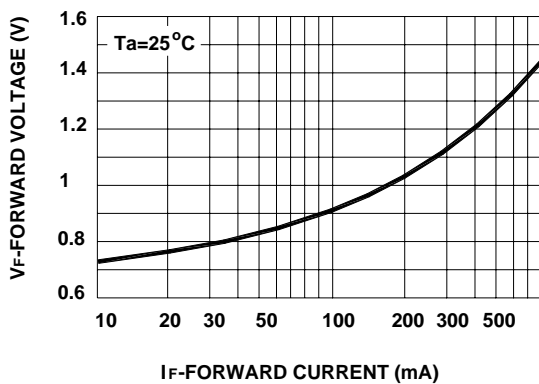
FORWARD VOLTAGE vs FORWARD CURRENT
VF-1 to 100 μ A



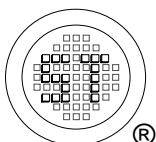
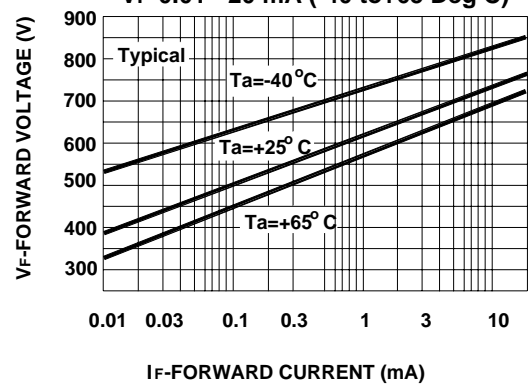
FORWARD VOLTAGE vs FORWARD CURRENT
VF-0.1 to 100 mA



FORWARD VOLTAGE vs FORWARD CURRENT
VF-10 to 800 mA



FORWARD VOLTAGE vs AMBIENT TEMPERATURE
Vf-0.01 - 20 mA (-40 to +65 Deg C)



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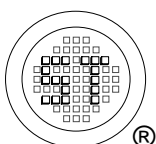
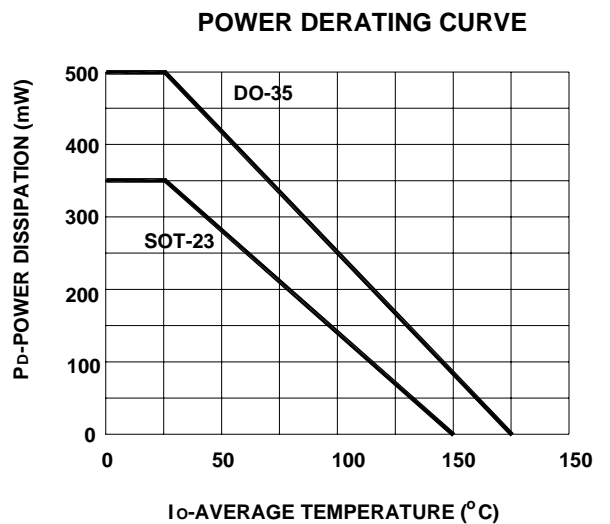
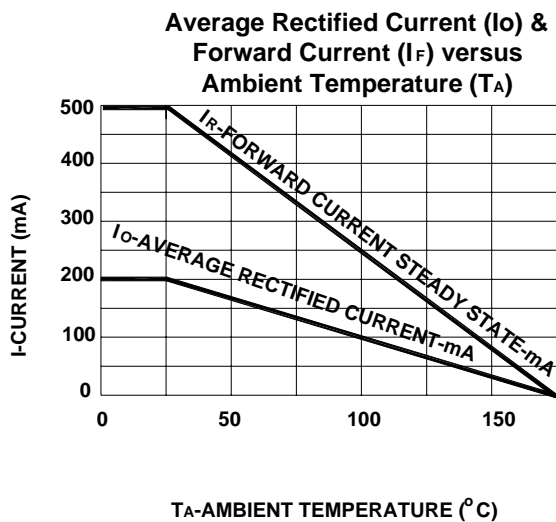
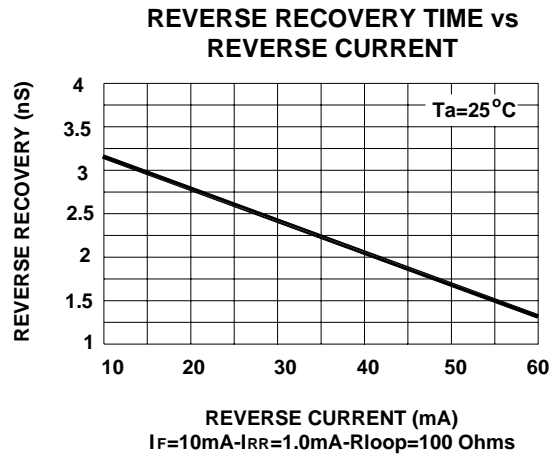
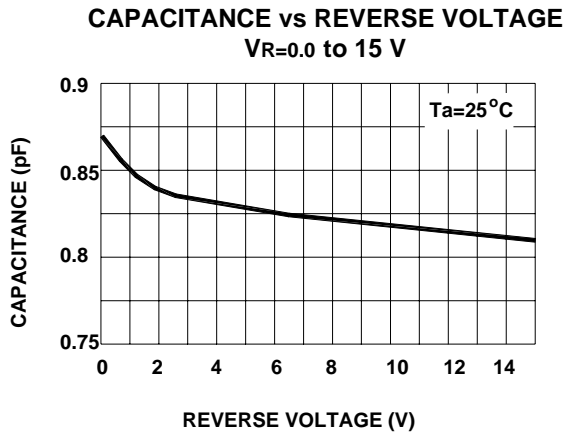
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Typical Characteristics



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